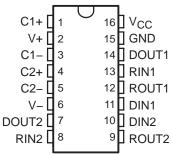


- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operates With 3-V to 5.5-V V<sub>CC</sub> Supply
- Operates Up To 250 kbit/s
- Two Drivers and Two Receivers
- Low Supply Current . . . 300 μA Typical
- External Capacitors . . .  $4 \times 0.1 \mu F$
- Accepts 5-V Logic Input With 3.3-V Supply
- Alternative High-Speed Pin-Compatible Device (1 Mbit/s) XL3232
- Applications
  - Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment

## D, DB, DW, OR PW PACKAGE (TOP VIEW)



#### ORDERING INFORMATION

TA	PACKAGI	<u>≡</u> †	TOP-SIDE MARKING
	COIC (D)	Tube of 40	
	SOIC (D)	Reel of 2500	XL3232
	0010 (0140	Tube of 40	ALOZOZ
00C to 700C	SOIC (DW)	Reel of 2000	
−0°C to 70°C	CCOD (DD)	Tube of 80	
	SSOP (DB)	Reel of 2000	XL3232DB
	TSSOP (PW)	Tube of 90	ALGEGEDE
		Reel of 2000	
	SOIC (D)	Tube of 40	
		Reel of 2500	XL3232I
	COIC (DW)	Tube of 40	AL32321
−40°C to 85°C	SOIC (DW)	Reel of 2000	
	CCOD (DD)	Tube of 80	
	SSOP (DB)	Reel of 2000	XL3232IP
	TCCOD (D\A\)	Tube of 90	ALOZOZII
	TSSOP (PW)	Reel of 2000	

1

The XL3232 device consists of two line drivers, two line receivers, and a dual charge-pump circuit with  $\pm 15$ -kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 250 kbit/s and a maximum of 30-V/ $\mu$ s driver output slew rate.

#### **Function Tables**

#### **EACH DRIVER**

INPUT DIN	OUTPUT DOUT
L	Н
Н	L

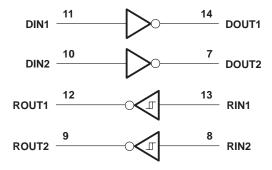
H = high level, L = low level

#### **EACH RECEIVER**

INPUT RIN	OUTPUT ROUT
L	Н
Н	L
Open	Н

$$\begin{split} H &= \text{high level, } L = \text{low} \\ \text{level, } Open &= \text{input} \\ \text{disconnected} & \text{or} \\ \text{connected driver off} \end{split}$$

### logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)	
Negative output supply voltage range, V- (see Note 1)	0.3 V to –7 V
Supply voltage difference, V+ - V- (see Note 1)	
Input voltage range, V <sub>I</sub> : Drivers	
Receivers	
Output voltage range, V <sub>O</sub> : Drivers	13.2 V to 13.2 V
	0.3 V to V <sub>CC</sub> + 0.3 V
Package thermal impedance, θ <sub>JA</sub> (see Notes 2 and 3):	: D package
	DB package 82°C/W
	DW package 57°C/W
	PW package 108°C/W
Operating virtual junction temperature, T.I	. •
Storage temperature range, T <sub>sta</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to network GND.
  - 2. Maximum power dissipation is a function of  $T_J(max)$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_J(max) T_A)/\theta_{JA}$ . Operating at the absolute maximum  $T_J$  of 150°C can affect reliability.
  - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

#### recommended operating conditions (see Note 4 and Figure 4)

				MIN	NOM	MAX	UNIT
	Supply voltage		V <sub>CC</sub> = 3.3 V	3	3.3	3.6	.,
			V <sub>CC</sub> = 5 V	4.5	5	5.5	V
.,	Deliver high level inner welfere	DIN	V <sub>CC</sub> = 3.3 V	2			V
VIH	Driver high-level input voltage		V <sub>CC</sub> = 5 V	2.4			V
V <sub>IL</sub>	Driver low-level input voltage		DIN			0.8	V
V	Driver input voltage		DIN	0		5.5	V
VI	Receiver input voltage			-25		25	V
Τ.			XL3232	0		70	00
TA	Operating free-air temperature			-40		85	· °C

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V $_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V $_{CC}$  = 5 V  $\pm$  0.5 V.

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

PARAMETER	TEST CONDITIONS	MIN TYP‡	MAX	UNIT
ICC Supply current	No load, $V_{CC} = 3.3 \text{ V or 5 V}$	0.3	1	mA

<sup>‡</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

#### **DRIVER SECTION**

### electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDI	TIONS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	DOUT at R <sub>L</sub> = $3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		V
VOL	Low-level output voltage	DOUT at R <sub>L</sub> = 3 k $\Omega$ to GND,	DIN = VCC	-5	-5.4		V
lн	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
Ι <sub>Ι</sub> L	Low-level input current	V <sub>I</sub> at GND			±0.01	±1	μΑ
la at	Chart singuit autout auront	V <sub>CC</sub> = 3.6 V,	VO = 0 V		125	-00	A
los‡	Short-circuit output current	V <sub>CC</sub> = 5.5 V,	VO = 0 V		±35	±60	mA
r <sub>O</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	V <sub>O</sub> = ±2 V	300	10M		Ω

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V $_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V $_{CC}$  = 5 V  $\pm$  0.5 V.

### switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
	Maximum data rate	C <sub>L</sub> = 1000 pF, One DOUT switching,	$R_L = 3 kΩ$ , See Figure 1	150	250		kbit/s
tsk(p)	Pulse skew§	C <sub>L</sub> = 150 pF to 2500 pF	$R_L$ = 3 kΩ to 7 kΩ, See Figure 2		300		ns
CD(4=)	Slew rate, transition region	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega$	C <sub>L</sub> = 150 pF to 1000 pF	6		30	1////
SR(tr) Siew rate, transition region (see Figure 1) $V_{CC} = 3.3 \text{ V}$	VCC = 3.3 V	C <sub>L</sub> = 150 pF to 2500 pF	4		30	V/μs	

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C. ‡ Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

<sup>§</sup> Pulse skew is defined as |tplH - tpHL| of each channel of the same device.

#### RECEIVER SECTION

### electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 4)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
Vон	High-level output voltage	I <sub>OH</sub> = -1 mA	VCC-0.6V	V <sub>CC</sub> -0.1 V		V
VOL	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
\/-	Decisive main a insent three held veltage	V <sub>CC</sub> = 3.3 V		1.5	2.4	.,
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.8	2.4	V
.,	N. d. i i i i i i i i i i i i i i i i i i	V <sub>CC</sub> = 3.3 V	0.6	1.2		.,
V <sub>IT</sub> _	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.8	1.5		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.3		V
rį	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

<sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V ± 0.5 V.

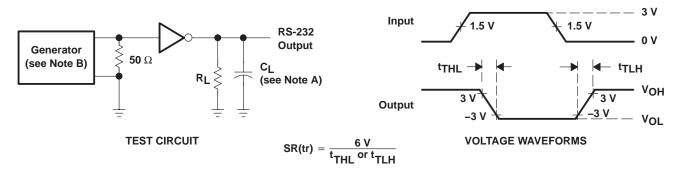
### switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 3)

PARAMETER		TEST CONDITIONS	MIN TYP <sup>†</sup> MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	O: 450 pF	300	ns
tPHL	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF	300	ns
tsk(p)	Pulse skew <sup>‡</sup>		300	ns

<sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

‡ Pulse skew is defined as  $|tp_{LH} - tp_{HL}|$  of each channel of the same device. NOTE 4: Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.

#### PARAMETER MEASUREMENT INFORMATION

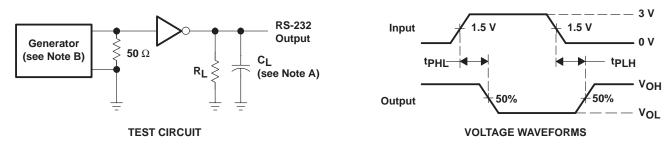


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \ \Omega$ , 50% duty cycle,  $t_\Gamma \le 10$  ns.

Figure 1. Driver Slew Rate

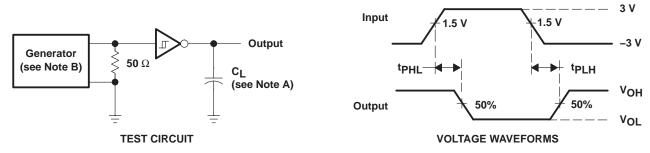
### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.

Figure 2. Driver Pulse Skew

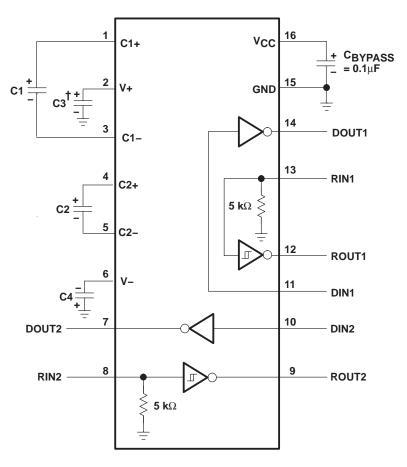


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.

Figure 3. Receiver Propagation Delay Times

### **APPLICATION INFORMATION**



 $<sup>^\</sup>dagger\text{C3}$  can be connected to VCC or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

**V<sub>CC</sub>** vs CAPACITOR VALUES

VCC	C1	C2, C3, C4
3.3 V ± 0.3 V 5 V ± 0.5 V 3 V to 5.5 V	0.1 μF 0.047 μF 0.1 μF	0.1 μF 0.33 μF 0.47 μF

**Figure 4. Typical Operating Circuit and Capacitor Values** 

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